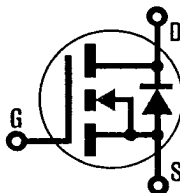


# HEXFET® TRANSISTORS IRFZ40 IRFZ42

**N-Channel  
50 VOLT  
POWER MOSFETs**



## 50 Volt, 0.028 Ohm HEXFET TO-220AB Plastic Package

The HEXFET technology has expanded its product base to serve the low voltage, very low  $R_{DS(on)}$  MOSFET transistor requirements. International Rectifier's highly efficient geometry and unique processing of the HEXFET have been combined to create the lowest on resistance per device performance. In addition to this feature all HEXFETs have documented reliability and parts per million quality!

The HEXFET transistors also offer all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

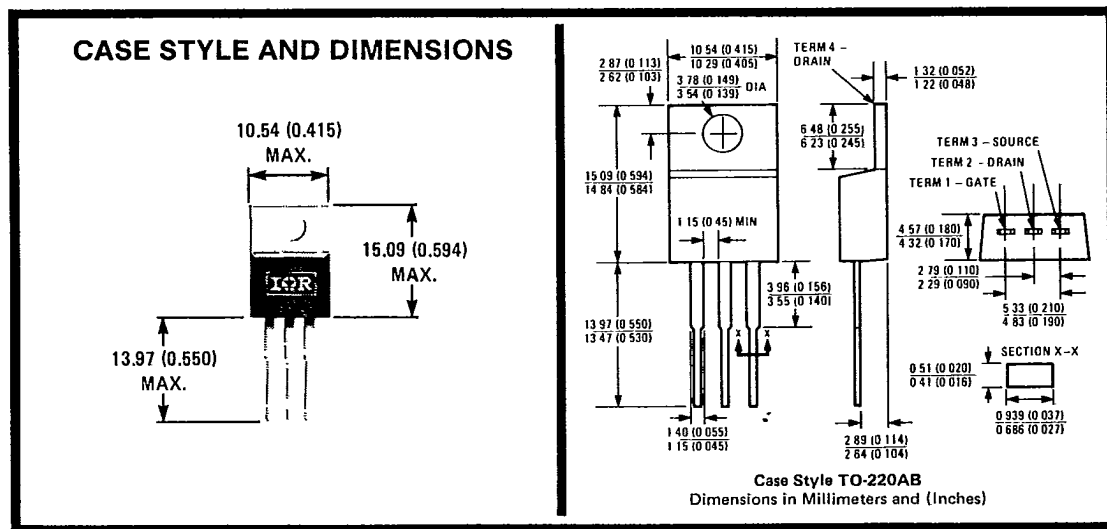
They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and in systems that are operated from low voltage batteries, such as automotive, portable equipment, etc.

## Product Summary

PART NUMBER	$V_{DS}$	$R_{DS(ON)}$	$I_D$
IRFZ40	50V	0.028 $\Omega$	35A*
IRFZ42	50V	0.035 $\Omega$	35A*

## Features:

- Extremely Low  $R_{DS(on)}$
- Compact Plastic Package
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability
- Parts Per Million Quality



\* $I_D$  Current limited by pin diameter

IRFZ40, IRFZ42 Series

INTERNATIONAL RECTIFIER

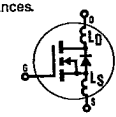
T-39-13

Absolute Maximum Ratings

Parameter	IRFZ40	IRFZ42	Units
V <sub>DS</sub> Drain - Source Voltage ①	50	50	V
V <sub>DGR</sub> Drain - Gate Voltage (R <sub>GS</sub> = 20 kΩ) ①	50	50	V
I <sub>D</sub> @ T <sub>C</sub> = 25°C Continuous Drain Current ④	35	35	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C Continuous Drain Current	32	29	A
I <sub>DM</sub> Pulsed Drain Current ⑤	160	145	A
V <sub>GS</sub> Gate - Source Voltage	±20		V
P <sub>D</sub> @ T <sub>C</sub> = 25°C Max. Power Dissipation	125 (See Fig. 14)		W
Linear Derating Factor	1.0 (See Fig. 14)		W/K ⑥
I <sub>LM</sub> Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH		A
	160	145	
T <sub>J</sub> Operating Junction and Storage Temperature Range	-55 to 150		°C
T <sub>stg</sub> Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		°C

Electrical Characteristics @ T<sub>C</sub> = 25°C (Unless Otherwise Specified)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV <sub>DSS</sub> Drain - Source Breakdown Voltage	IRFZ40	50	—	—	V	V <sub>GS</sub> = 0V I <sub>D</sub> = 250 μA
	IRFZ42	50	—	—	V	
V <sub>GS(th)</sub> Gate Threshold Voltage	ALL	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA
I <sub>GSS</sub> Gate-Source Leakage Forward	ALL	—	—	500	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub> Gate-Source Leakage Reverse	ALL	—	—	-500	nA	V <sub>GS</sub> = -20V
I <sub>DSS</sub> Zero Gate Voltage Drain Current	ALL	—	—	250	μA	V <sub>DS</sub> = Max. Rating, V <sub>GS</sub> = 0V
		—	—	1000	μA	V <sub>DS</sub> = Max. Rating × 0.8, V <sub>GS</sub> = 0V, T <sub>C</sub> = 125°C
I <sub>D(on)</sub> On-State Drain Current ② ③	IRFZ40	35	—	—	A	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , V <sub>GS</sub> = 10V
	IRFZ42	35	—	—	A	
R <sub>DS(on)</sub> Static Drain-Source On-State Resistance ③	IRFZ40	—	0.024	0.028	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 29A
	IRFZ42	—	0.030	0.035	Ω	
g <sub>fs</sub> Forward Transconductance ②	ALL	17	22	—	S(Ω)	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 29A
C <sub>iss</sub> Input Capacitance	ALL	—	2380	3000	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1.0 MHz
C <sub>oss</sub> Output Capacitance	ALL	—	920	1200	pF	See Fig. 10
C <sub>rss</sub> Reverse Transfer Capacitance	ALL	—	250	400	pF	
t <sub>d(on)</sub> Turn-On Delay Time	ALL	—	18	25	ns	V <sub>DD</sub> ≈ 25V, I <sub>D</sub> = 29A, Z <sub>o</sub> = 4.7Ω
t <sub>r</sub> Rise Time	ALL	—	25	60	ns	See Fig. 17
t <sub>d(off)</sub> Turn-Off Delay Time	ALL	—	35	70	ns	(MOSFET switching times are essentially independent of operating temperature.)
t <sub>f</sub> Fall Time	ALL	—	12	25	ns	
Q <sub>g</sub> Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	—	40	60	nC	V <sub>GS</sub> = 10V, I <sub>D</sub> = 64A, V <sub>DS</sub> = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q <sub>gs</sub> Gate-Source Charge	ALL	—	22	—	nC	
Q <sub>gd</sub> Gate-Drain ("Miller") Charge	ALL	—	18	—	nC	
L <sub>D</sub> Internal Drain Inductance	ALL	—	3.5	—	nH	Measured from the contact screw on tab to center of die.
		—	4.5	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
L <sub>S</sub> Internal Source Inductance	ALL	—	7.5	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.



Thermal Resistance

Parameter	Units	Value	Notes
R <sub>thJC</sub> Junction-to-Case	W/K ⑦	1.0	
R <sub>thCS</sub> Case-to-Sink	W/K ⑧	—	Mounting surface flat, smooth, and greased.
R <sub>thJA</sub> Junction-to-Ambient	W/K ⑧	80	Typical socket mount

IRFZ40, IRFZ42 Series

INTERNATIONAL RECTIFIER

T-39-13

Source-Drain Diode Ratings and Characteristics

$I_S$	Continuous Source Current (Body Diode)	IRFZ40	—	—	35	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRFZ42	—	—	35	A	
$I_{SM}$	Pulse Source Current (Body Diode) ③	IRFZ40	—	—	160	A	
		IRFZ42	—	—	145	A	
$V_{SD}$	Diode Forward Voltage ②	IRFZ40	—	—	2.5	V	$T_C = 25^\circ\text{C}, I_S = 51\text{A}, V_{GS} = 0\text{V}$
		IRFZ42	—	—	2.2	V	$T_C = 25^\circ\text{C}, I_S = 46\text{A}, V_{GS} = 0\text{V}$
$t_{rr}$	Reverse Recovery Time	ALL	—	350	—	ns	$T_J = 150^\circ\text{C}, I_F = 51\text{A}, di/dt = 100\text{A}/\mu\text{s}$
$Q_{RR}$	Reverse Recovered Charge	ALL	—	2.1	—	$\mu\text{C}$	$T_J = 150^\circ\text{C}, I_F = 51\text{A}, di/dt = 100\text{A}/\mu\text{s}$
$t_{on}$	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$ .				

- ①  $T_J = 25^\circ\text{C}$  to  $150^\circ\text{C}$ .
- ② Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).
- ④  $I_D$  Current limited by pin diameter.
- ⑤  $KW = \text{ }^\circ\text{C}/\text{W}$   
 $W/K = \text{ }^\circ\text{C}/\text{W}$

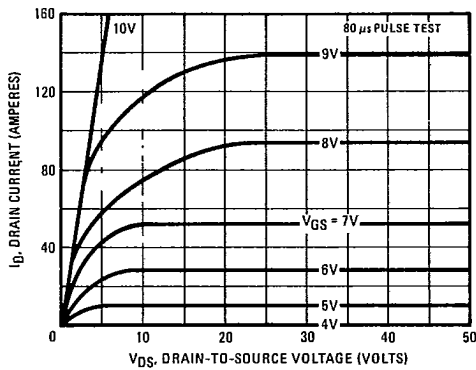


Fig. 1 - Typical Output Characteristics

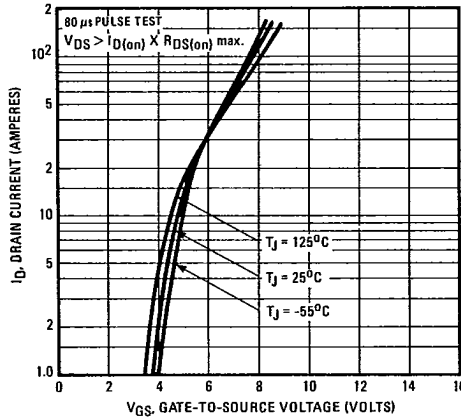


Fig. 2 - Typical Transfer Characteristics

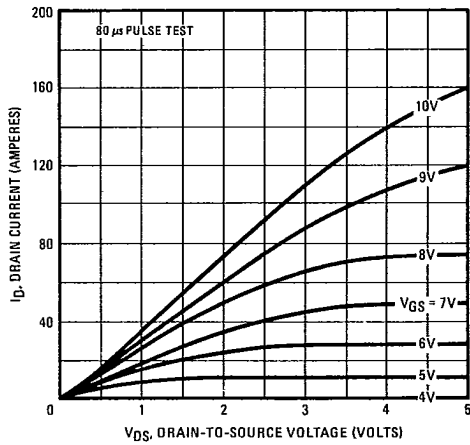


Fig. 3 - Typical Saturation Characteristics

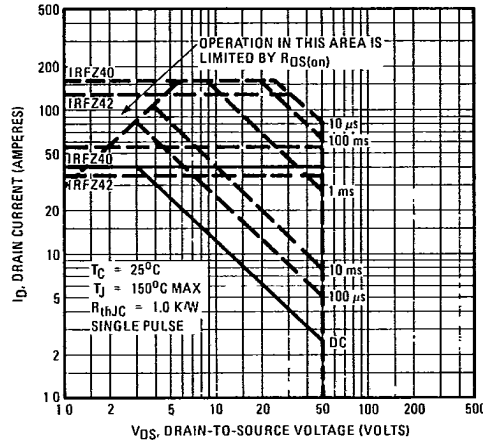


Fig. 4 - Maximum Safe Operating Area

C-443

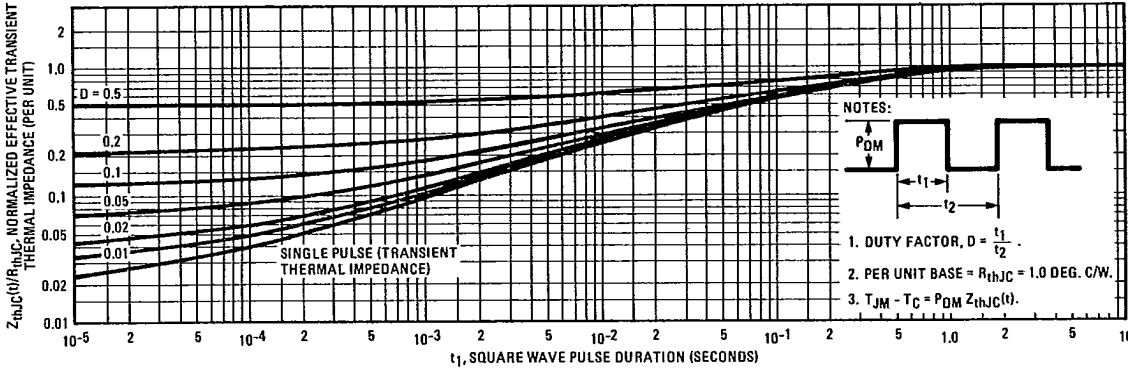


Fig. 5 – Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

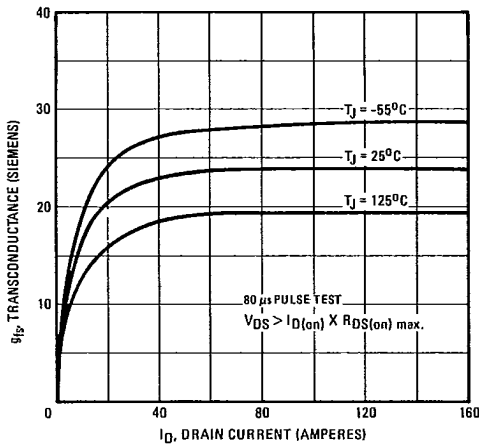


Fig. 6 – Typical Transconductance Vs. Drain Current

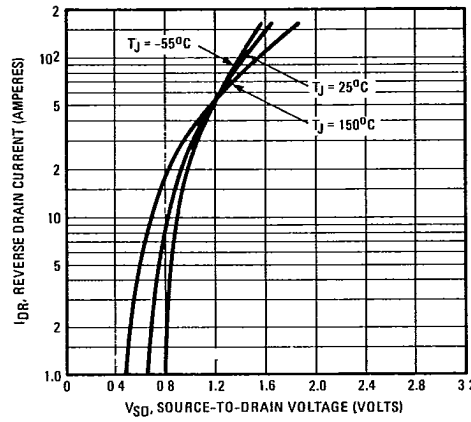


Fig. 7 – Typical Source-Drain Diode Forward Voltage

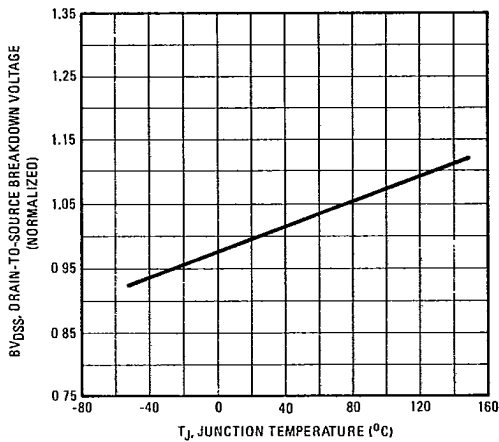


Fig. 8 – Breakdown Voltage Vs. Temperature

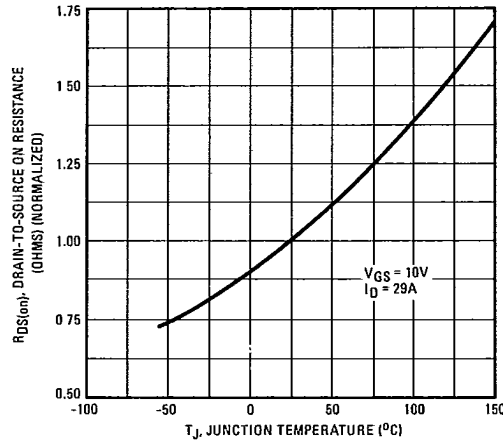


Fig. 9 – Normalized On-Resistance Vs. Temperature

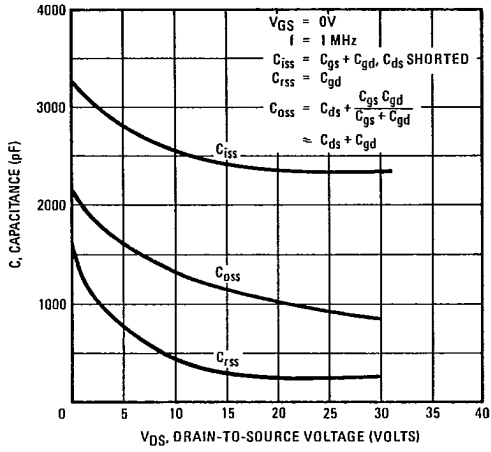


Fig. 10 - Typical Capacitance Vs. Drain-to-Source Voltage

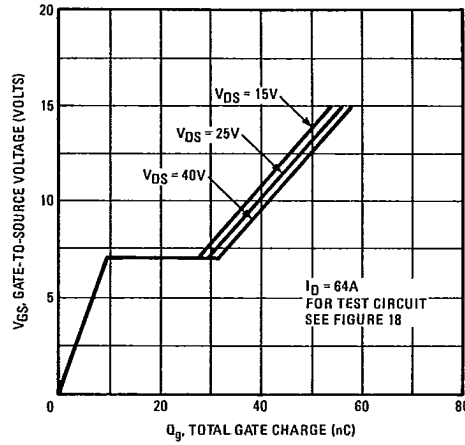


Fig. 11 - Typical Gate Charge Vs. Gate-to-Source Voltage

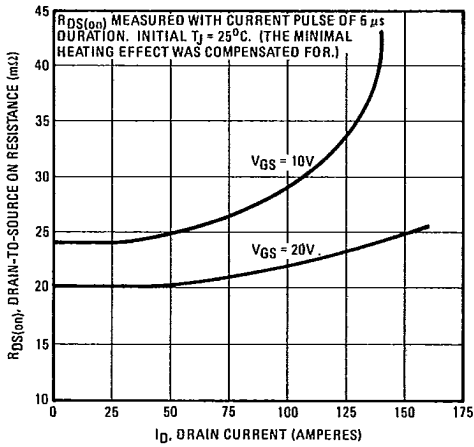


Fig. 12 - Typical On-Resistance Vs. Drain Current

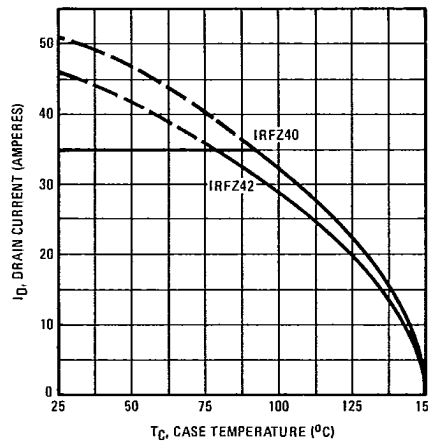


Fig. 13 - Maximum Drain Current Vs. Case Temperature

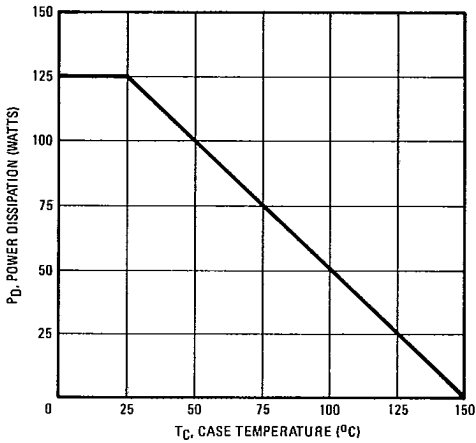


Fig. 14 - Power Vs. Temperature Derating Curve

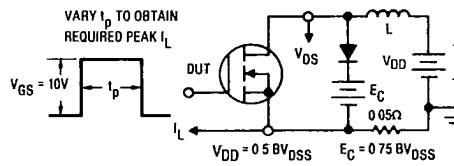


Fig. 15 - Clamped Inductive Test Circuit

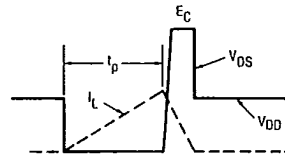


Fig. 16 - Clamped Inductive Waveforms

IRFZ40, IRFZ42 Series

INTERNATIONAL RECTIFIER

T-39-13

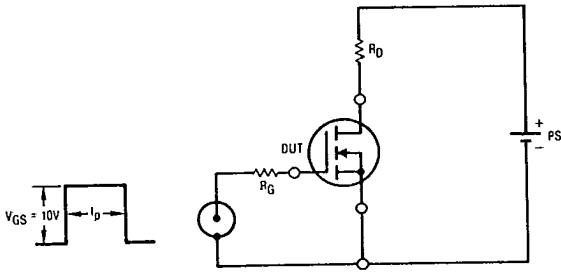


Fig. 17 — Switching Time Test Circuit

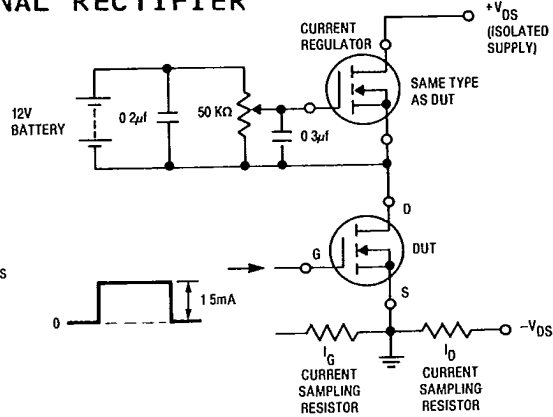
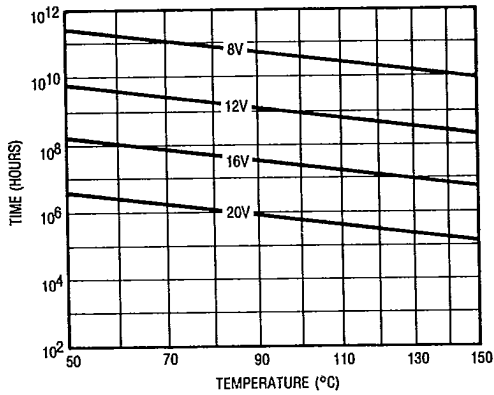
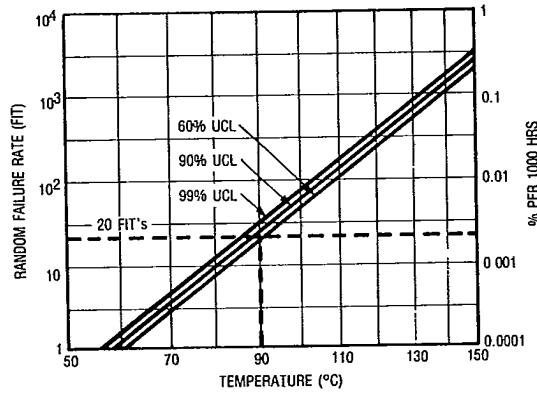


Fig. 18 — Gate Charge Test Circuit



\*Fig. 19 — Typical Time to Accumulated 1% Failure



\*Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

\*The data shown is correct as of April 15, 1987. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.